



INFORMATION DISCLOSURE CITATION
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APPLICANT(S):

BRIAN G. JOHNSON

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GROUP ART UNIT:

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>A.S.</i>	A.	5,166,758	11/24/1992	OVSHINSKY ET AL.	257	3	
	B.						
	C.						
	D.						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION IF APPROPRIATE	
	E.						YES	NO
	F.							
	G.							

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

<i>A.S.</i>	H.	Hwang, Y.N., Hong, J.S., Lee, S.H., Ahn, S.J., Jeong, G.T., Koh, G.H., Kim, H.J., Jeong, W.C., Lee, S.Y., Park, J.H., Ryoo, K.C., Horii, H., Ha, Y.H., Yi, J.H., Cho, W.Y., Kim, Y.T., Lee, K.H., Joo, S.H., Park, S.O., Jeong, U.I., Jeong, H.S. and Kim, Kinam, "Completely CMOS-Compatible Phase-Change Nonvolatile RAM Using NMOS Cell Transistors," presented at 2003 19 th IEEE Non-Volatile Semiconductor Memory Workshop, Monterey, California, February 26-20, 2003
<i>A.S.</i>	I.	Ha, Y.H., Yi, J.H., Horii, H., Park, J.H., Joo, S.H., Park, S.O., Chung, U-In and Moon, J.T., "An Edge Contact Type Cell for Phase Change RAM Featuring Very Low Power Consumption," presented at IEEE 2003 Symposium on VLSI Technology, Kyoto, Japan, June 12-14, 2003
<i>A.S.</i>	J.	Hwang, Y.N., Hong, J.S., Lee, S.H., Ahn, S.J., Jeong, G.T., Koh, G.H., Oh, J.H., Kim, H.J., Jeong, W.C., Lee, S.Y., Park, J.H., Ryoo, K.C., Horii, H., Ha, Y.H., Yi, J.H., Cho, W.Y., Kim, Y.T., Lee, K.H., Joo, S.H., Park, S.O., Chung, U.I., Jeong, H.S. and Kim, Kinam, "Full Integration and Reliability Evaluation of Phase-change RAM Based on 0.24 mm-CMOS Technologies," presented at IEEE 2003 Symposium on VLSI Technology, Kyoto, Japan, June 12-14, 2003
<i>A.S.</i>	K.	Horii, H., Yi, J.H., Park, J.H., Ha, Y.H., Baek, I.G., Park, S.O., Hwang, Y.N., Lee, S.H., Kim, Y.T., Lee, K.H., Chung, U-In and Moon, J.T., "A Novel Cell Technology Using N-doped GeSbTe Films for Phase Change RAM," presented at IEEE 2003 Symposium on VLSI Technology, Kyoto, Japan, June 12-14, 2003
<i>A.S.</i>	L.	Wicker, G.C., "Phase Change Memory and Method Therefor", U.S. Patent Application Serial No. 10/318,984, filed December 13, 2002
<i>A.S.</i>	M.	Wicker, G.C., "Lateral Phase Change Memory and Method Therefor", U.S. Patent Application Serial No. 10/319,204, filed December 13, 2002
	N.	

EXAMINER

DATE CONSIDERED

12/10/04

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.